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Applicati n Number	09/945,507	
Filing Date	August 30, 2001	
First Named Inventor	Forbes, Leonard	
Group Art Unit	2824	
Examiner Name	Dinh, Son	

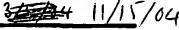
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Attorne	y Docket	No:	1303	.014US1
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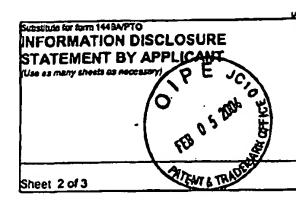
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Examiner Name	Dinh, Son

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on of information unless it contains a valid OMB control number.

Substitute for form 1449A/PTO Complete If Known INFORMATION DISCLOSURE 09/945,507 **Application Number** STATEMENT BY APPLICANE
(Use as many sheets as necessary) August 30, 2001 Filing Date Forbes, Leonard **First Named Inventor** 2824 **Group Art Unit** Dinh, Son **Examiner Name** Attorney Docket No: 1303.014US1 Sheet 1 of 1

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First Named Inventor

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